Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- · Enhanced power dissipation capability of 1390 mW

3. Applications

- · Relay driver
- High-speed line driver
- · High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-7	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -5.3 \text{ A}; T_j = 25 \text{ °C}$		-	28	34	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



20 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol
D	drain	<u> </u>	D
D	drain		
G	gate		G \downarrow \downarrow \downarrow
S	source	TSOP6 (SOT457)	
D	drain		
D	drain		S 017aaa259
	D D S D	D drain D drain G gate S source D drain	D drain D drain G gate S source D drain TSOP6 (SOT457)

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN30XPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN30XPE	3F

20 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-7	Α
		V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-5.3	Α
		V_{GS} = -4.5 V; T_{amb} = 100 °C	[1]	-	-3.4	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-21	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	560	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	6.25	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

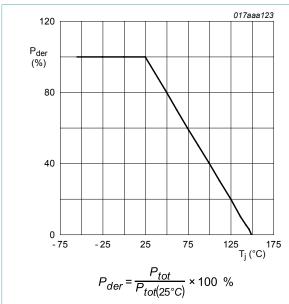


Fig. 1. Normalized total power dissipation as a function of junction temperature

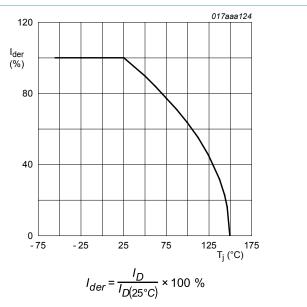


Fig. 2. Normalized continuous drain current as a function of junction temperature

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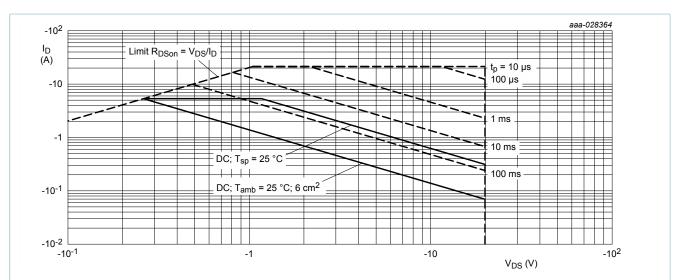


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

20 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	195	225	K/W
	from junction to ambient		[2]	-	78	90	K/W
		in free air, t ≤ 5 s	[2]	-	45	52	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

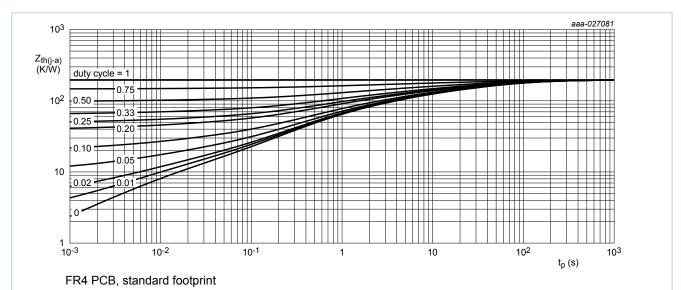


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

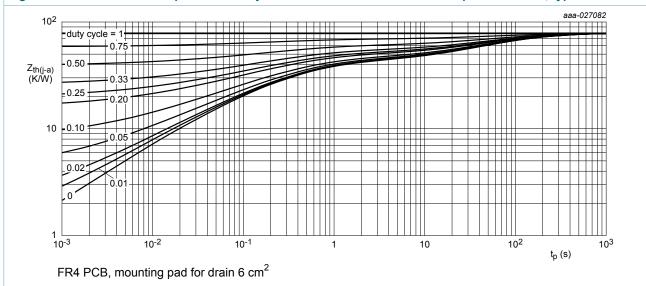


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μΑ
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		$V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
DOON	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -5.3 A; T_j = 25 °C	-	28	34	mΩ
		V _{GS} = -4.5 V; I _D = -5.3 A; T _j = 150 °C	-	40	49	mΩ
		V_{GS} = -2.5 V; I_D = -4.1 A; T_j = 25 °C	-	42	57	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C	-	13	-	S
R_G	gate resistance	f = 1 MHz	-	10.4	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -3 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	11	17	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	2	-	nC
Q_{GD}	gate-drain charge		-	2.5	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}$; f = 1 MHz; $V_{GS} = 0 \text{ V}$;	-	1465	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	193	-	pF
C _{rss}	reverse transfer capacitance		-	133	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -3 A; V_{GS} = -4.5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	27	-	ns
t _{d(off)}	turn-off delay time		-	62	-	ns
t _f	fall time		-	28	-	ns
Source-dra	in diode		'			
V _{SD}	source-drain voltage	I _S = -1.4 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.7	-1.2	V

20 V, P-channel Trench MOSFET

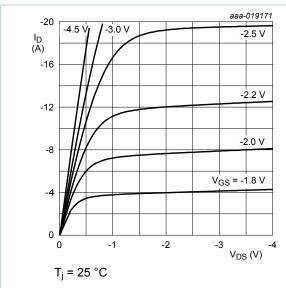


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

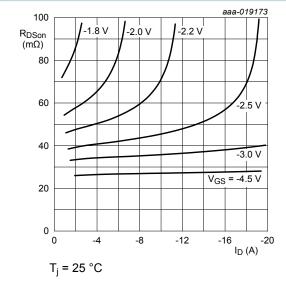


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

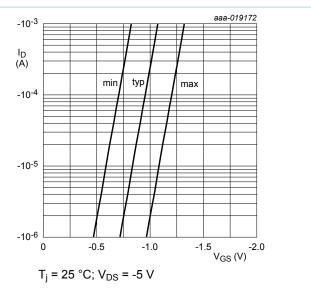


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

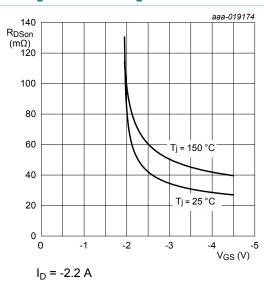


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

20 V, P-channel Trench MOSFET

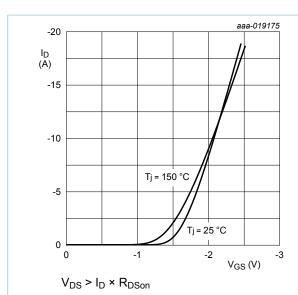


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

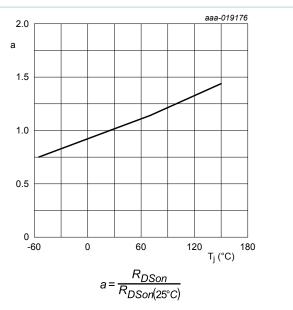


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

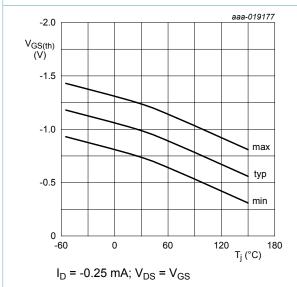


Fig. 12. Gate-source threshold voltage as a function of junction temperature

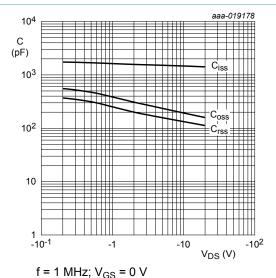


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

20 V, P-channel Trench MOSFET

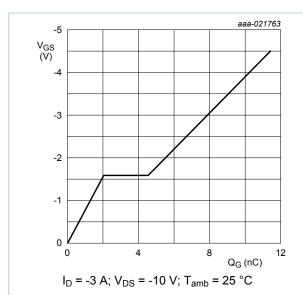


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

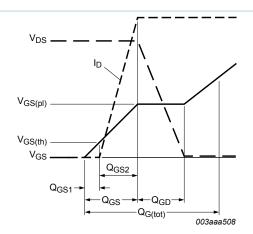


Fig. 15. Gate charge waveform definitions

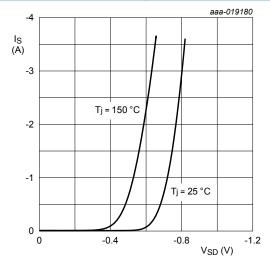
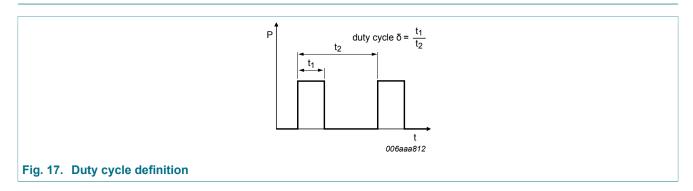


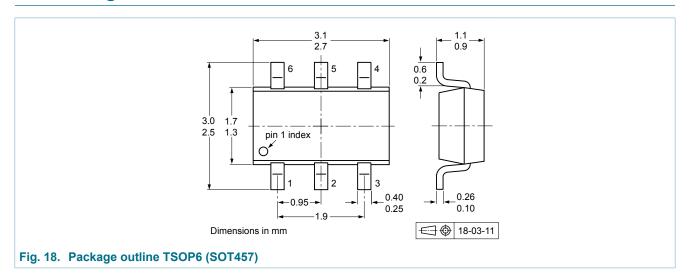
Fig. 16. Source current as a function of source-drain voltage; typical values

20 V, P-channel Trench MOSFET

11. Test information

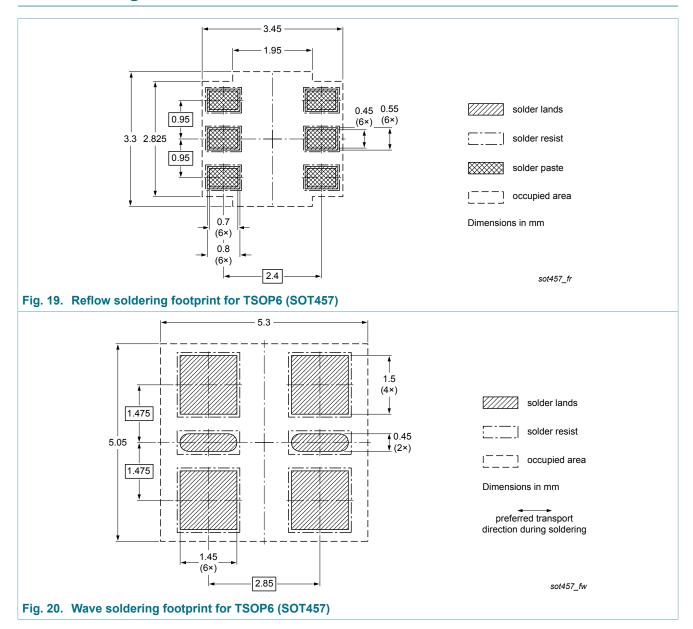


12. Package outline



20 V, P-channel Trench MOSFET

13. Soldering



20 V, P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN30XPE v.1	20180416	Product data sheet	-	-

20 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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20 V, P-channel Trench MOSFET

16. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	Characteristics	6
11.	Test information	. 10
12.	Package outline	10
13.	Soldering	11
14.	Revision history	.12
15.	Legal information	13

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